



MATERIALS AND ENERGY – Vol. 1

HANDBOOK OF INSTRUMENTATION AND TECHNIQUES FOR SEMICONDUCTOR NANOSTRUCTURE CHARACTERIZATION

Editors

Richard Haight • Frances M Ross • James B Hannon

IBM TJ Watson Research Center, USA

with Foreword by Leonard C. Feldman



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CONTENTS

Foreword	xvii
Introduction	xxi

VOLUME 1

ELECTRON MICROSCOPIES

1. Characterization of Semiconductor Nanostructures by Scanning Electron Microscopy	1
<i>Lynne M. Gignac and Oliver C. Wells</i>	
1.1. Introduction	3
1.2. SEM Instrumentation	4
1.2.1. Electron Sources	6
1.2.2. Electron Lenses	8
1.2.3. Electron Detectors	11
1.2.4. Beam Deceleration/Sample Bias	15
1.2.5. Aberration Correction	16
1.2.6. Focused Ion Beam Systems	20
1.3. Practical Examples	22
1.3.1. Imaging with Low Incident Beam Energy	22
1.3.2. Electron Beam Induced Sample Damage	23
1.3.3. Use of Sample Bias/Beam Deceleration	24
1.3.4. Use of a Source Monochromator	26
1.3.5. Secondary Electron Detectors	28

1.3.6.	Use of STEM Detector	31
1.3.7.	Imaging with High Incident Beam Energy	32
1.4.	Conclusions	39
	References	40
2.	Transmission Electron Microscopy and Ultra-high Vacuum Transmission Electron Microscopy of Semiconductor Nanostructures <i>Suneel Kodambaka and Frances M. Ross</i>	43
2.1.	Introduction to TEM and UHV TEM	44
2.2.	TEM of Semiconductor Nanostructures	46
2.2.1.	Sample Preparation	46
2.2.1.1.	Freestanding nanostructures	47
2.2.1.2.	Embedded or Epitaxial nanostructures	48
2.2.2.	High Resolution Imaging: Local Structure, Strain and Composition	51
2.2.3.	Bright Field and Dark Field Imaging: Strain Fields and Dislocations	54
2.2.4.	Analytical TEM: Composition and Bonding Within Nanostructures	57
2.2.5.	<i>In situ</i> TEM: Electrical, Mechanical and Growth Measurements Nanostructures	59
2.2.6.	Some Issues to Consider for TEM	61
2.3.	Ultra-High Vacuum Transmission Electron Microscopy	63
2.3.1.	Experimental Aspects of UHV TEM	63
2.3.1.1.	Microscope design	64
2.3.1.2.	Sample preparation	66
2.3.1.3.	Some issues to consider for UHV TEM	67
2.3.2.	Plan View Bright and Dark Field Imaging: Ge Quantum Dot Growth on Si(001)	68
2.3.3.	Reflection Mode Imaging: Si and Ge Nanowire Growth	71

2.3.3.1.	Extending the range of nanowire growth experiments	74
2.3.3.2.	Electrical measurements in UHV TEM	74
2.3.4.	Plan View Imaging and Diffraction: Thin Film Silicide Reactions	75
2.3.5.	Plan View Imaging and Diffraction: Silicide Islands	77
2.3.5.1.	Compact silicide islands	77
2.3.5.2.	Silicide nanowires	79
2.3.6.	Bright Field, Dark Field and High Resolution Imaging: Nanoscale Phase Transitions	81
2.4.	Summary and Outlook	82
	References	84
3.	Aberration Corrected Electron Microscopy	89
	<i>Philip E. Batson</i>	
3.1.	Introduction	89
3.2.	Multipole Correction for the STEM	95
3.3.	Measurement and Control of Aberration Optics	98
3.4.	Stability Improvements Needed to Make Aberration Correction Successful	101
3.5.	Aberration Nomenclature and Probe Properties	105
3.6.	Improvement in Images of Semiconductors	107
3.7.	New Capability Enabled by Aberration Correction	112
3.8.	Next Generation Equipment	120
3.9.	Conclusions	122
	References	122
4.	Low-Energy Electron Microscopy for Nanoscale Characterization	127
	<i>James B. Hannon and Rudolf M. Tromp</i>	
4.1.	Introduction	128
4.2.	LEEM/PEEM Instrumentation	129
4.2.1.	The Cathode Objective Lens and Limit Resolution	129

4.2.2.	A Simple PEEM Instrument	134
4.2.3.	A "Simple" LEEM Instrument	138
4.2.4.	Energy Filtered LEEM/PEEM	143
4.2.5.	Aberration Correction	149
4.2.6.	Further Developments	151
4.3.	Applications of LEEM	153
4.3.1.	LEEM Contrast	153
4.3.2.	Selected Area Diffraction	157
4.3.3.	Dark-field Imaging	159
4.3.4.	Quantitative LEED Analysis	162
4.3.5.	Quantum Well States	164
4.3.6.	Fingerprinting	166
4.3.7.	Quantitative LEED at the Nanoscale	167
4.3.8.	Inelastic Imaging in LEEM	173
4.4.	Conclusion	177
	References	179
5.	Ultrafast Microscopy of Plasmon Dynamics in Nanostructured Metal Surfaces <i>Hrvoje Petek and Atsushi Kubo</i>	183
5.1.	Introduction	184
5.2.	Ultrafast Multidimensional Microscopy	185
5.2.1.	Laser Pump-Electron Probe Methods	185
5.2.2.	Laser Pump-Probe Photoelectron Imaging Methods	187
5.2.3.	Interferometric Time-Resolved Photoemission Electron Microscopy	188
5.3.	ITR-PEEM Measurements	191
5.3.1.	Ultrafast Imaging of Plasmonic Phenomena	191
5.3.1.1.	Localized surface plasmons	192
5.3.1.2.	Surface plasmon polaritons	193
5.3.1.3.	Imaging of plasmonic excitations	194
5.3.2.	Ultrafast ITR-PEEM Imaging of Localized Surface Plasmon Modes	196
5.3.2.1.	Imaging of plasmonic hot-spots	196
5.3.2.2.	ITR-PEEM imaging of SP dephasing	199

5.3.3.	Ultrafast ITR-PEEM Imaging of Surface Plasmon Polaritons	200
5.4.	Conclusions and Outlook	206
	References	207
6.	X-ray Diffraction Methods for Studying Strain and Composition in Epitaxial Nanostructured Systems <i>Angelo Malachias, Raul Freitas, Sérgio L. Morelhão, Rogério Magalhães-Paniago, Stefan Kycia and Gilberto Medeiros-Ribeiro</i>	211
6.1.	Introduction	212
6.2.	Atomic Scattering Factor and Anomalous Diffraction	214
6.2.1.	Atomic Form Factor	215
6.2.2.	Anomalous (Resonant) X-ray Scattering	216
6.3.	Form Factor of a Small Crystal	220
6.4.	Structure Factor	222
6.5.	Coplanar and Grazing-Incidence Diffraction	225
6.6.	Bragg-Surface Diffraction	230
6.7.	Evaluation of Strain in Nanostructures	233
6.7.1.	Polar Diagrams and Sample Preparation Procedures	233
6.7.2.	Uncapped Nanostructures	235
6.7.2.1.	The Ge:Si(001) system	235
6.7.2.2.	In-plane strain analysis	237
6.7.2.3.	Pseudomorphic relaxation	241
6.7.3.	Capped Nanostructures	245
6.7.3.1.	Renninger scanning and three-dimensional lattice parameter determination	245
6.7.3.2.	BSD mesh-scans and capping process defects	251
6.8.	Chemical Composition Analysis by Anomalous X-ray Diffraction	254
6.8.1.	Composition in Two-Element Systems	254
6.8.2.	Complementary Anomalous X-ray Diffraction — InP:GaAs(001)	257

6.8.3.	Three-Dimensional Composition in Uncapped Islands	266
6.9.	Addressing Elastic, Thermodynamical and Growth Properties	272
6.10.	Conclusions	275
	References	276
7.	Stress Determination in Semiconductor Nanostructures Using X-ray Diffraction <i>Conal E. Murray and I. Cevdet Noyan</i>	281
7.1.	Introduction	282
7.2.	Basic X-ray Analysis Techniques	284
7.2.1.	X-ray Diffraction	284
7.2.2.	Kinematical Diffraction Theory	284
7.2.3.	Strain	287
7.2.4.	Effect of Sample Heterogeneity	288
7.3.	Information Volume of X-ray Techniques	291
7.4.	Focusing of X-rays	292
7.4.1.	Refractive Optics	293
7.4.2.	Reflective Optics	294
7.4.2A.	Capillary Optics	294
7.4.2B.	X-ray Mirrors	294
7.4.3.	Diffractive Optics	295
7.4.3A.	Fresnel Zone-Plates	295
7.5.	Applications	295
7.5.1.	Experimental Considerations	296
7.5.2.	Silicon-on-insulator (SOI) Structures	297
7.5.2A	Measurement of SOI Channel Strain Induced by Embedded Stressor Materials	298
7.5.2B	SOI Strain Distributions Generated by Overlying Stressor Materials	303
7.5.3.	Topographic Studies	307
7.5.3A	SiGe Features on Si(001)	307
7.6.	Conclusions	311
	References	311